



#### P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
	120mΩ @ V <sub>GS</sub> = -4.5V	
-20V	150mΩ @ V <sub>GS</sub> = -2.5V	-3A

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

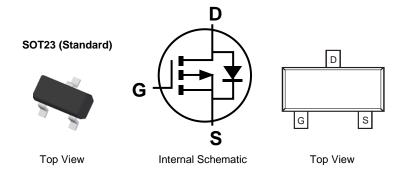
- Backlighting
- Power Management Functions
- DC-DC Converters
- Motor Control

### **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. <a href="https://www.diodes.com/quality/product-definitions/">https://www.diodes.com/quality/product-definitions/</a>

#### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 63
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



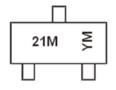
# Ordering Information (Note 4)

Part Number	Case	Packaging
DMG2301L-7	SOT23 (Standard)	3,000/Tape & Reel
DMG2301L-13	SOT23 (Standard)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



21M = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: I = 2021) M = Month (ex: 9 = September)

#### Date Code Key

Year	2014		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	В		ı	J	K	L	М	N	0	Р	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		$V_{DSS}$	-20	V	
Gate-Source Voltage		Vgss	±8	V	
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	I <sub>D</sub>	-3 -1	А		
Pulsed Drain Current (Note 6)		I <sub>DM</sub>	-10	Α	
Drain-Source Diode Forward Current (t < 5 sec)			Is	-0.75	Α

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	1.5	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	$R_{\theta JA}$	83	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

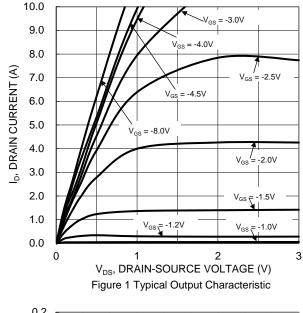
## Electrical Characteristics (@TA = +25°C, unless otherwise specified)

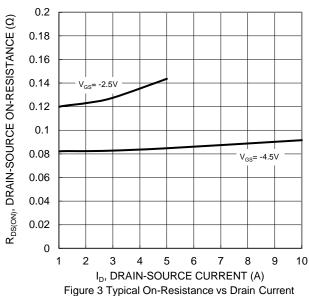
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Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage		BVDSS	-20	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> =	+25°C	I <sub>DSS</sub>	_		-1.0	μΑ	$V_{DS} = -16V, V_{GS} = 0V$
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 6V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		V <sub>GS(TH)</sub>	-0.4		-1.2	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$
Static Drain-Source On-Resistance		Dagger			120	mΩ	$V_{GS} = -4.5V$ , $I_{D} = -2.8A$
Static Dialii-Source Off-Nesistance		RDS(ON)			150	11152	$V_{GS} = -2.5V$ , $I_D = -2.0A$
Diode Forward Voltage		VsD	_	_	-1.2	V	$V_{GS} = 0V$ , $I_{S} = -0.75A$
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance		Ciss	_	476		pF	101/11/ 01/
Output Capacitance		Coss	_	53	_	pF	$V_{DS} = -10V, V_{GS} = 0V$ - $f = 1.0MHz$
Reverse Transfer Capacitance		$C_{rss}$	_	45		pF	1 – 1.000112
Total Gate Charge		$Q_g$	_	5.5	_	nC	
Gate-Source Charge		$Q_{gs}$	_	0.9	_	nC	$V_{GS} = -4.5V$ , $V_{DS} = -6V$ , $I_{D} = -2.8A$
Gate-Drain Charge		$Q_{gd}$	_	1.8	_	nC	
Turn-On Delay Time		tD(ON)	_	5	_	ns	
Turn-On Rise Time		tR	_	10	_	ns	$V_{DS} = -6V, V_{GS} = -4.5V,$
Turn-Off Delay Time		tD(OFF)	_	30	_	ns	RGEN = $6\Omega$ , ID = -1A
Turn-Off Fall Time	•	t <sub>F</sub>		20	_	ns	

Notes:

- 5. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
- 6. Repetitive rating, pulse width limited by junction temperature.
- 7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to production testing.







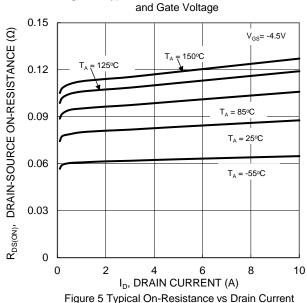
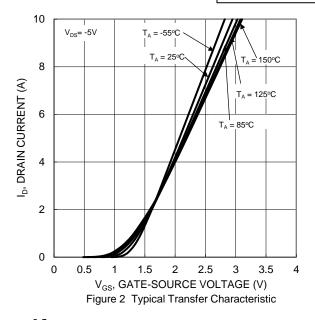
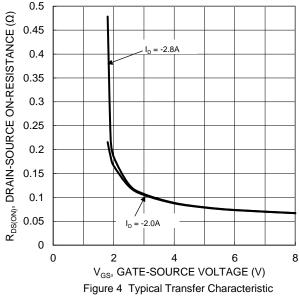


Figure 5 Typical On-Resistance vs Drain Current and Temperature





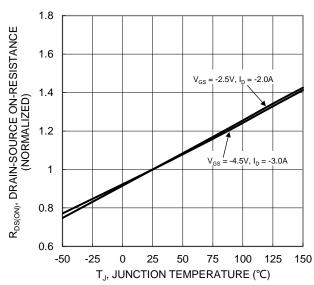
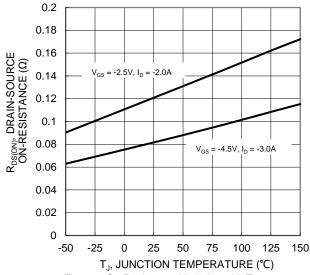
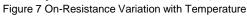


Figure 6 On-Resistance Variation with Temperature







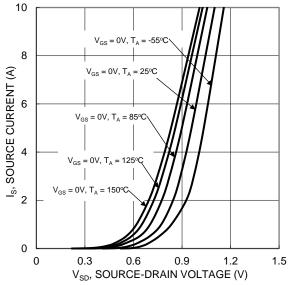
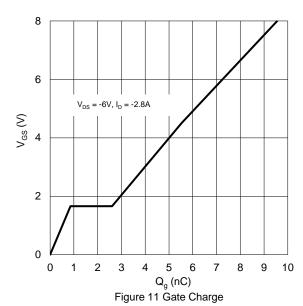


Figure 9 Diode Forward Voltage vs. Current



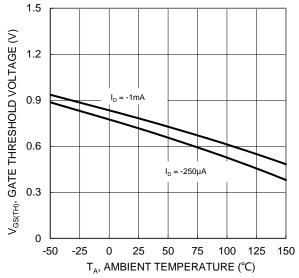
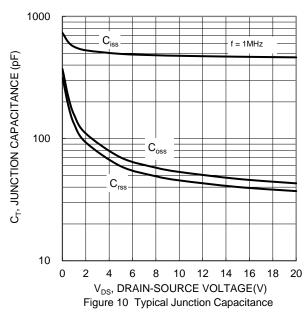
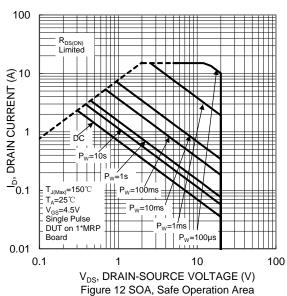


Figure 8 Gate Threshold Variation vs Ambient Temperature







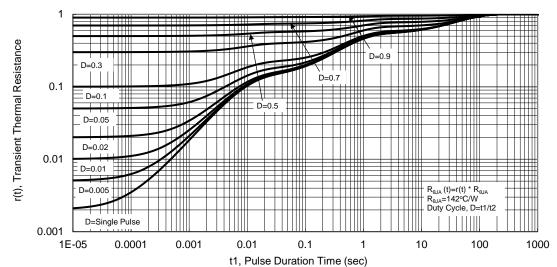


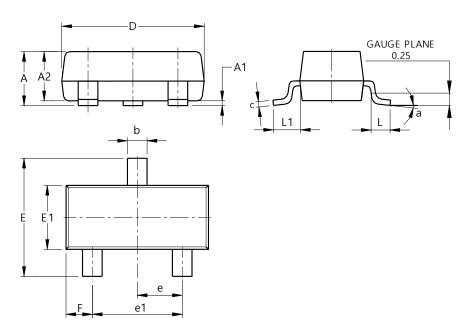
Figure 13 Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23 (Standard)

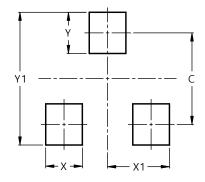


SOT23 (Standard)								
Dim	Min	Max	Тур					
Α	0.90	1.15	1.025					
A1	0.00	0.10	0.05					
A2	0.85	1.10	0.975					
b	0.30	0.51	0.40					
С	0.080	0.202	0.11					
D	2.80	3.00	2.90					
Е	2.25	2.55	2.40					
E1	1.20	1.40	1.30					
е	0.89	1.03	0.915					
e1	1.78	2.05	1.83					
F	0.40	0.60	0.535					
L1	0.45	0.61	0.55					
L	0.25	0.55	0.40					
а	0°	8°						
All Dimensions in mm								

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23 (Standard)



Dimensions	Value (in mm)				
С	2.0				
Х	0.8				
X1	1.35				
Y	0.9				
Y1	29				



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